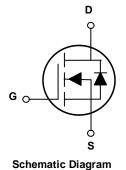


### **Main Product Characteristics**

V <sub>(BR)DSS</sub>	30V		
R <sub>DS(ON)</sub>	27mΩ		
ID	5.6A		





SOT-23

### **Features and Benefits**

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



### **Description**

The GSF3400 utilizes the latest techniques to achieve ultral high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in battery protection, load switch, power management and a wide variety of other applications.

### **Absolute Maximum Ratings** (T<sub>A</sub>=25°C unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-to-Source Voltage	V <sub>GS</sub>	± 12	V
Continuous Drain Current, @ Steady-State	I <sub>D</sub> @ T <sub>A</sub> = 25°C	5.6	А
Continuous Drain Current, @ Steady-State	I <sub>D</sub> @ T <sub>A</sub> = 70°C	4.5	А
Pulsed Drain Current <sup>1</sup>	I <sub>DM</sub>	23	А
Power Dissipation	P <sub>D</sub> @T <sub>A</sub> = 25°C	1.2	W
Junction-to-Ambient (PCB Mounted, Steady-State) <sup>2</sup>	R <sub>0JA</sub>	104	°C/W
Operating Junction and Storage Temperature Range	T <sub>J</sub> T <sub>STG</sub>	-55 to + 150	°C



# **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise specified)

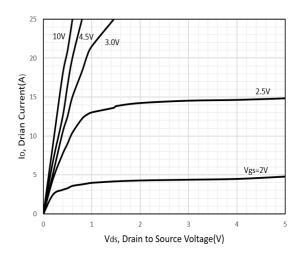
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	30	-	_	V	
Drain-to-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V	-	-	1	μА	
		T <sub>J</sub> = 125°C	-	-	50		
O-t- t- O 5	I <sub>GSS</sub>	V <sub>GS</sub> =12V	-	-	100	nA	
Gate-to-Source Forward Leakage		V <sub>GS</sub> = -12V	-	-	-100		
Static Drain-to-Source On-	R <sub>DS (on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> = 5.6A	-	21	27		
Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> = 5.0A	D = 5.0A 25 33		mΩ		
		V <sub>GS</sub> =2.5V, I <sub>D</sub> = 3.0A	-	33	51		
Gate Threshold Voltage	V <sub>GS (th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.65	0.9	1.5	V	
Input Capacitance	$C_{iss}$		-	535	-	pF	
Output Capacitance	$C_{oss}$	$V_{GS} = 0V V_{DS} = 15V f$ = 1MHz	-	130	-		
Reverse transfer capacitance	$C_{rss}$		-	36	-		
Total Gate Charge	$Q_{g}$		-	4.8	-	nC	
Gate-to-Source Charge	$Q_gs$	I <sub>D</sub> =5.6A, V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V	-	1.2	-		
Gate-to-Drain("Miller") Charge	$Q_{gd}$		-	1.7	-		
Turn-on Delay Time	$t_{d(on)}$		-	12	-	nS	
Rise Time	tr	$V_{GS}$ =4.5V, $V_{DS}$ =15V, $R_L$ =15 $\Omega$ ,	-	52	-		
Turn-Off Delay Time	$t_{d(off)}$	$R_{GEN}$ =2.8Ω $I_D$ =1A	-	17	-		
Fall Time	t <sub>f</sub>		-	10	-		
Source-Drain Ratings and Charac	teristics						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Continuous Source Current (Body Diode)	ls	MOSFET symbol showing the integral reverse	-	-	5.6	А	
Pulsed Source Current (Body Diode)	I <sub>SM</sub>	p-n junction diode.	-	-	23	Α	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =5.6A, V <sub>GS</sub> =0V	-	0.8	1.2	V	

#### Notes

- 1. Pulse test: Pulse Width≤300us, Duty cycle ≤2%.
- 2. Device mounted on FR-4 PCB, 1inch x 0.85inch x 0.062 inch.



# **Typical Electrical and Thermal Characteristic Curves**



**Figure 1. Typical Output Characteristics** 

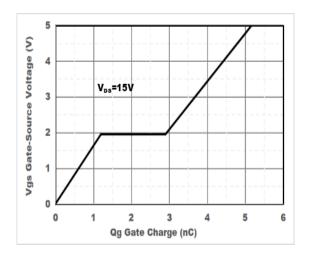


Figure 2. Transfer Characteristics

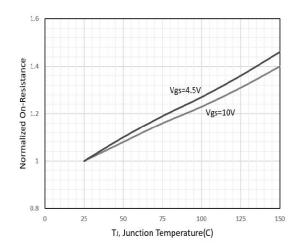


Figure 3. Gate Charge.

Figure 4. Normalized On-Resistance Vs. Junction Temperature



# **Typical Electrical and Thermal Characteristic Curves**

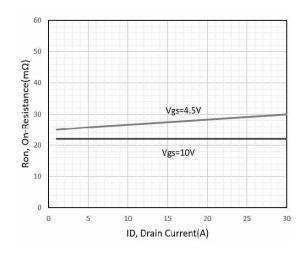


Figure 5. Drain-Source On-Resistance

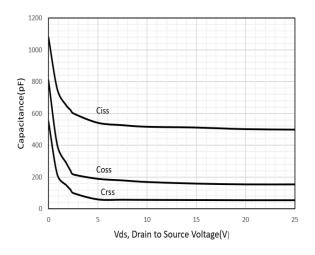


Figure 6. Typical Capacitance Vs. Drain-to-Source Voltage

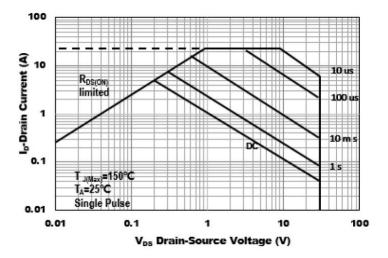


Figure 7. Safe Operation Area



### **Test Circuit & Waveform**

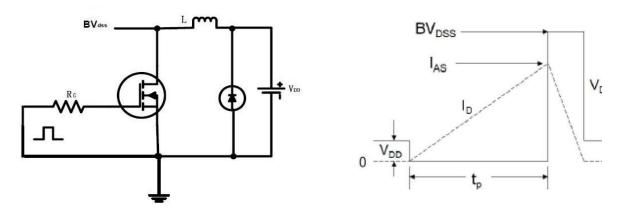


Figure 8. Unclamped Inductive Switching Test Circuit & Waveforms

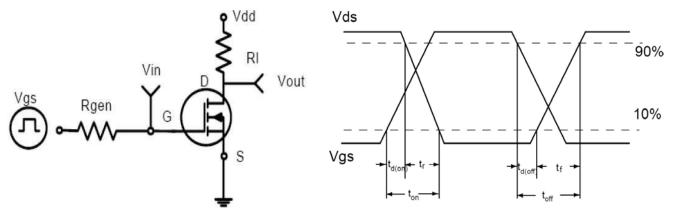


Figure 9. Resistive Switching Test Circuit & Waveforms

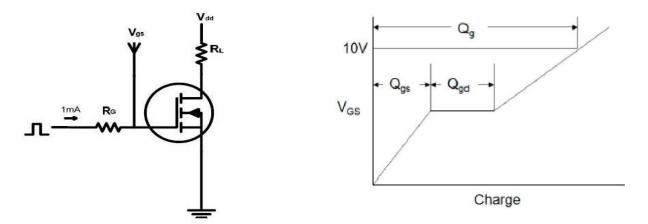
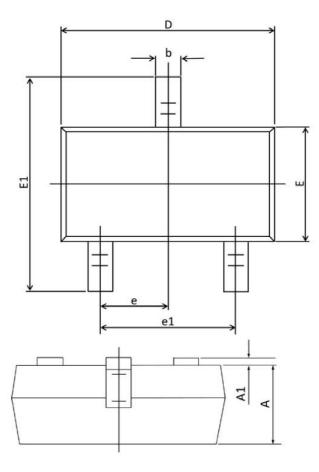


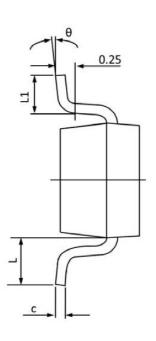
Figure 10. Gate Charge Test Circuit & Waveform



# **Package Outline Dimensions**







Cymahal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.000	0.035	0.039	
A1	0.000	0.100	0.000	0.004	
b	0.300	0.500	0.012	0.020	
С	0.090	0.110	0.003	0.004	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP.		0.037 TYP.		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF.		0.022 REF.		
L1	0.300	0.500	0.012	0.020	
θ	1°	7°	1°	7°	